Refine Search



Search Results -

Terms	Documents
L3 and (fluorinated or fluorine or fluorinate)	3

US Pre-Grant Publication Full-Text Database US Patents Full-Text Database

Database:

US OCR Full-Text Database EPO Abstracts Database JPO Abstracts Database Derwent World Patents Index IBM Technical Disclosure Bulletins

Search:

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Recall Text 🗢	Clea

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Search History

DATE: Thursday, June 24, 2004 Printable Copy Create Case

<u>Set Nam</u> side by sid	<u>e Query</u>	Hit Count	<u>Set Name</u> result set
•	ISPT; PLUR=YES; OP=ADJ		icsuit set
<u>L9</u>	L3 and (fluorinated or fluorine or fluorinate)	3	<u>1.9</u>
<u>L8</u>	L6 and (fluorinated or fluorine or fluorinate)	0	<u>L8</u>
<u>L7</u>	L6 and (fluorinated)	0	<u>1.7</u>
<u>L.6</u>	L3 and (silicon adj dioxide)	11	<u>L6</u>
<u>1.5</u>	L3 and (cyclobutane or polyarylene)	0	<u>1.5</u>
<u>L.4</u>	L3 and (spin near3 glass)	4	<u>L4</u>
<u>L.3</u>	L2 and (anisotropically near2 (etch or etching))	28	<u>1.3</u>
<u>L2</u>	L1 and mask	254	<u>L2</u>
$\mathbb{L}1$	fourth adj dielectric	730	<u>L1</u>

END OF SEARCH HISTORY

Clear Generate Collection Print Fwd Refs Bkwd Refs
Generate OACS

Search Results - Record(s) 1 through 3 of 3 returned.

1. Document ID: US 6225207 B1

L9: Entry 1 of 3

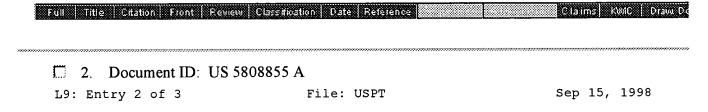
File: USPT

May 1, 2001

US-PAT-NO: 6225207

DOCUMENT-IDENTIFIER: US 6225207 B1

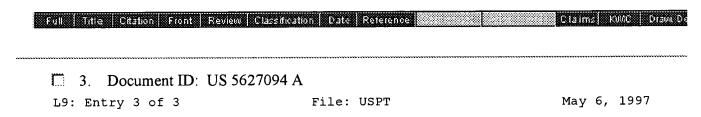
TITLE: Techniques for triple and quadruple damascene fabrication



US-PAT-NO: 5808855

DOCUMENT-IDENTIFIER: US 5808855 A

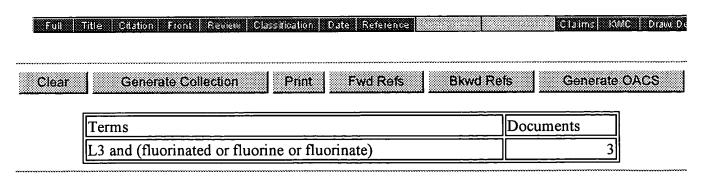
TITLE: Stacked container capacitor using chemical mechanical polishing



US-PAT-NO: 5627094

DOCUMENT-IDENTIFIER: US 5627094 A

TITLE: Stacked container capacitor using chemical mechanical polishing



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Generate OACS

Search Results - Record(s) 1 through 4 of 4 returned.

1. Document ID: US 6225207 B1

L4: Entry 1 of 4

File: USPT

May 1, 2001

US-PAT-NO: 6225207

DOCUMENT-IDENTIFIER: US 6225207 B1

TITLE: Techniques for triple and quadruple damascene fabrication

Full Title Citation Front Review Classication Date Received:

Claims NAME Draw Oc

Claims NAME Draw Oc

Claims NAME Draw Oc

L4: Entry 2 of 4 File: USPT Sep 15, 1998

US-PAT-NO: 5808855

DOCUMENT-IDENTIFIER: US 5808855 A

TITLE: Stacked container capacitor using chemical mechanical polishing

US-PAT-NO: 5627094

DOCUMENT-IDENTIFIER: US 5627094 A

TITLE: Stacked container capacitor using chemical mechanical polishing

Full Title Citation Front Review Classification Date Reference Claims AMC Draw Du

T 4. Document ID: US 4696097 A

L4: Entry 4 of 4 File: USPT . Sep 29, 1987

US-PAT-NO: 4696097

DOCUMENT-IDENTIFIER: US 4696097 A

TITLE: Poly-sidewall contact semiconductor device method

Generate Collection Pri	nt Fwd Refs Bkwd Refs Ger	nerate O/
T	Desuments	
Terms	Documents	
L3 and (spin near3 glass)		4

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Clear Generate Collection Print Fwd Refs Bkwd Refs
Generate OACS

Search Results - Record(s) 1 through 10 of 11 returned.

1. Document ID: US 6706608 B2

L6: Entry 1 of 11

File: USPT

Mar 16, 2004

Nov 6, 2001

US-PAT-NO: 6706608

DOCUMENT-IDENTIFIER: US 6706608 B2

TITLE: Memory cell capacitors having an over/under configuration

Full Title Citation Front Review Classification Date Retained Classification Date Classifi

US-PAT-NO: 6518670

DOCUMENT-IDENTIFIER: US 6518670 B1

TITLE: Electrically porous on-chip decoupling/shielding layer

US-PAT-NO: 6399480

DOCUMENT-IDENTIFIER: US 6399480 B1

TITLE: Methods and arrangements for insulating local interconnects for improved alignment tolerance and size reduction

Full Title Citation Front Review Classification Date Reference Claims KWC Draw D.

1. 4. Document ID: US 6312966 B1

File: USPT

US-PAT-NO: 6312966

L6: Entry 4 of 11

DOCUMENT-IDENTIFIER: US 6312966 B1

TITLE: Method of forming sharp tip for field emission display

Full Title Citation Front Review Classification Date Reference Claims KMiC Draw.D.

5. Document ID: US 6121663 A

L6: Entry 5 of 11

File: USPT

Sep 19, 2000

US-PAT-NO: 6121663

DOCUMENT-IDENTIFIER: US 6121663 A

TITLE: Local interconnects for improved alignment tolerance and size reduction

Full Title Citation Front Review Classification Date Reference Claims KWIC Draw De

6. Document ID: US 6031445 A

L6: Entry 6 of 11

File: USPT

Feb 29, 2000

US-PAT-NO: 6031445

DOCUMENT-IDENTIFIER: US 6031445 A

TITLE: Transformer for integrated circuits

Full Title Citation Front Review Classification Date Reference Claims KiMC Draw Do 7. Document ID: US 5930668 A Jul 27, 1999

File: USPT

US-PAT-NO: 5930668

L6: Entry 7 of 11

DOCUMENT-IDENTIFIER: US 5930668 A

TITLE: Process of fabricating embedded ground plane and shielding structures using

sidewall insulators in high frequency circuits having vias

Full Title Citation Front Review Classification Date Reference Claims KMC Draw Do

8. Document ID: US 5386088 A

L6: Entry 8 of 11

File: USPT

Jan 31, 1995

US-PAT-NO: 5386088

DOCUMENT-IDENTIFIER: US 5386088 A

TITLE: Embedded ground plane and shielding structures using sidewall insulators in

high frequency circuits having vias

Full Title Citation Front Review Classification Date Reference Claims KNNC Drawibe

9. Document ID: US 5285017 A

L6: Entry 9 of 11

File: USPT

Feb 8, 1994

US-PAT-NO: 5285017

DOCUMENT-IDENTIFIER: US 5285017 A

TITLE: Embedded ground plane and shielding structures using sidewall insulators in

high frequency circuits having vias

US-PAT-NO: 4851078

DOCUMENT-IDENTIFIER: US 4851078 A

TITLE: Dielectric isolation process using double wafer bonding

Full Title Citation Front Review Classification Date I	Reference Calcium (AU)Calcium Drema Dr
44	d Refs Bkwd Refs Generate OACS
Terms	Documents
L3 and (silicon adj dioxide)	11

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Search Results - Record(s) 11 through 11 of 11 returned.

11. Document ID: US 4728606 A

L6: Entry 11 of 11

File: USPT

Mar 1, 1988

US-PAT-NO: 4728606

DOCUMENT-IDENTIFIER: US 4728606 A

TITLE: Self-aligned transistor method

Full	itle Citation Front Review Classification	Date Reference		Claims RWC Draw D
Clear	Generate Collection Print	Fwd Refs	Bkwd Refs	Generate OACS
[Terms	- inches	Documents	
	L3 and (silicon adj dioxide)			11

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